

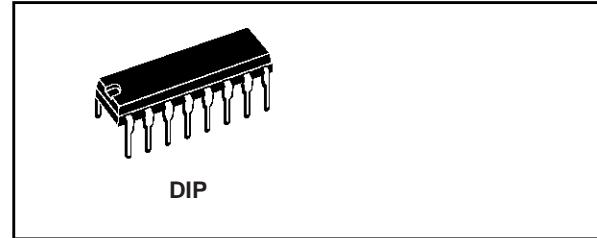


上海双岭电子有限公司

CC4044

## QUAD NAND 3-STATE R-S LATCH

- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 3-LEVEL OUTPUTS WITH COMMON OUTPUT ENABLE
- SEPARATE SET AND RESET INPUT FOR EACH LATCH
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT  
 $I_I = 100\text{nA}$  (MAX) AT  $V_{DD} = 18\text{V}$   $T_A = 25^\circ\text{C}$
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



### ORDER CODES

PACKAGE	TUBE	T & R
DIP	CC4044	

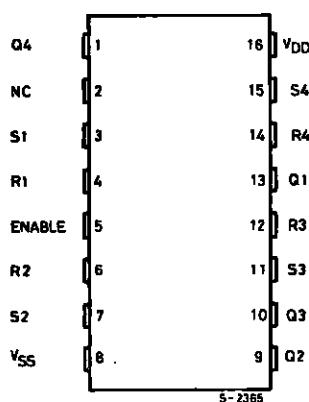
### DESCRIPTION

The CC4044 is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. The CC4044 is a quad cross-coupled 3-state CMOS NAND latch.

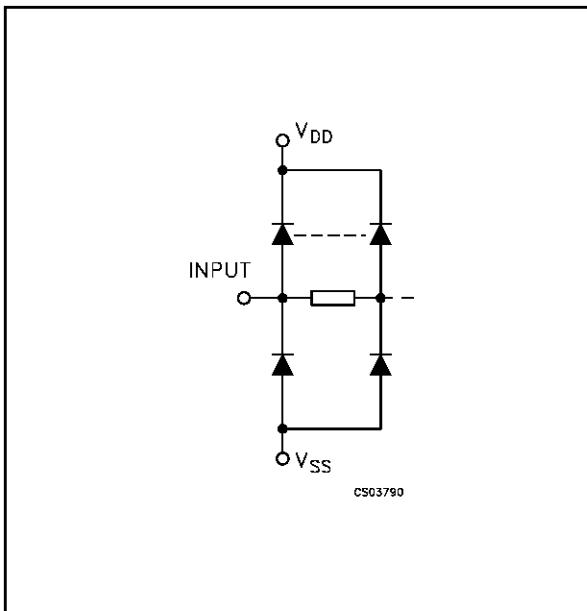
Each latch has a separate Q output and individual SET and RESET input. The Q outputs are

controlled by a common ENABLE input. A logic "1" or "high" on the ENABLE inputs connects the latch states to the Q outputs. A logic "0" or "low" on the ENABLE input disconnects the latch states from the Q outputs, resulting in an open circuit condition on the Q outputs. The open circuit feature allows common bussing of the outputs.

### PIN CONNECTION



## INPUT EQUIVALENT CIRCUIT



## PIN DESCRIPTION

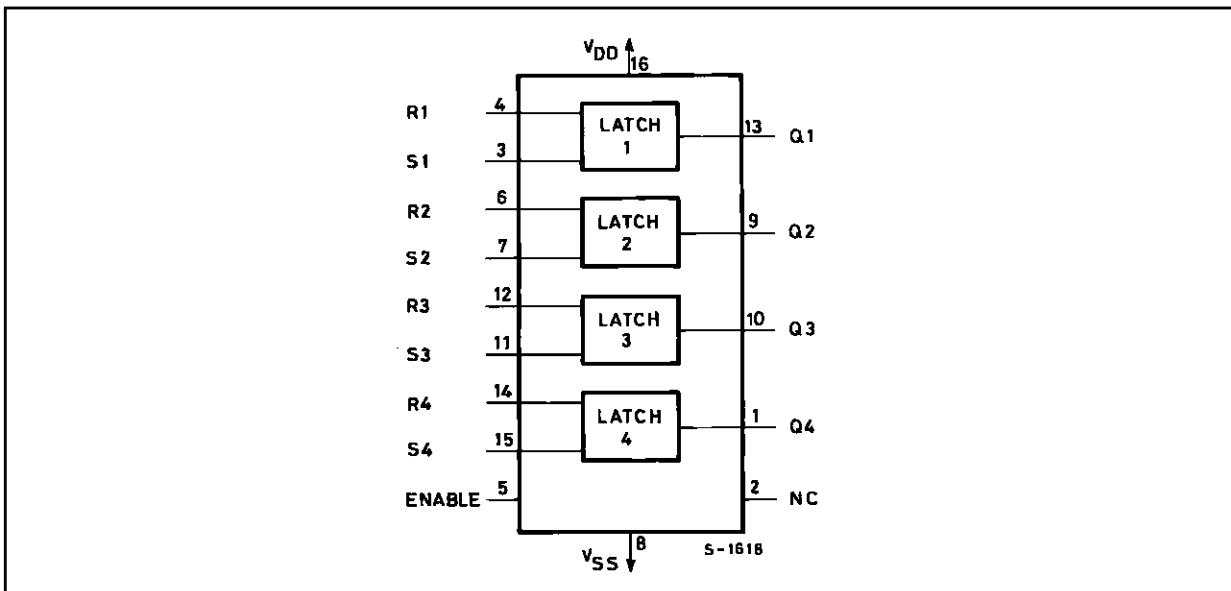
PIN No	SYMBOL	NAME AND FUNCTION
4, 6, 12, 14	S1 to S4	Set Inputs
3, 7, 11, 15	R1 to R4	Reset Inputs
5	ENABLE	Enable Input
13, 9, 10, 1	Q1 to Q4	Outputs
2	NC	Not Connected
8	V <sub>SS</sub>	Negative Supply Voltage
16	V <sub>DD</sub>	Positive Supply Voltage

## TRUTH TABLE

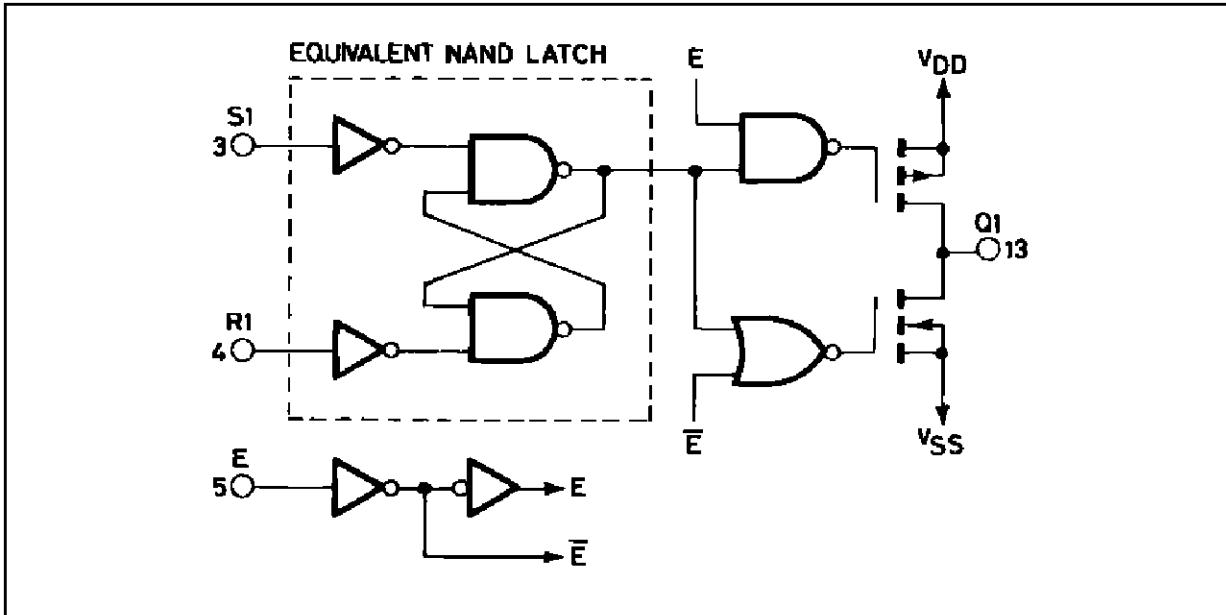
INPUTS			OUTPUT Q <sub>n</sub>
ENABLE	S <sub>n</sub>	R <sub>n</sub>	
L	X	X	Z
H	L	H	H
H	X	L	L
H	L	H	LATCHED

X : Don't Care

## FUNCTIONAL DIAGRAM



## LOGIC DIAGRAM



## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage	-0.5 to +20	V
$V_I$	DC Input Voltage	-0.5 to $V_{DD} + 0.5$	V
$I_I$	DC Input Current	$\pm 10$	mA
$P_D$	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
$T_{op}$	Operating Temperature	-55 to +125	°C
$T_{stg}$	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to  $V_{SS}$  pin voltage.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage	3 to 18	V
$V_I$	Input Voltage	0 to $V_{DD}$	V
$T_{op}$	Operating Temperature	-55 to 125	°C

## DC SPECIFICATIONS

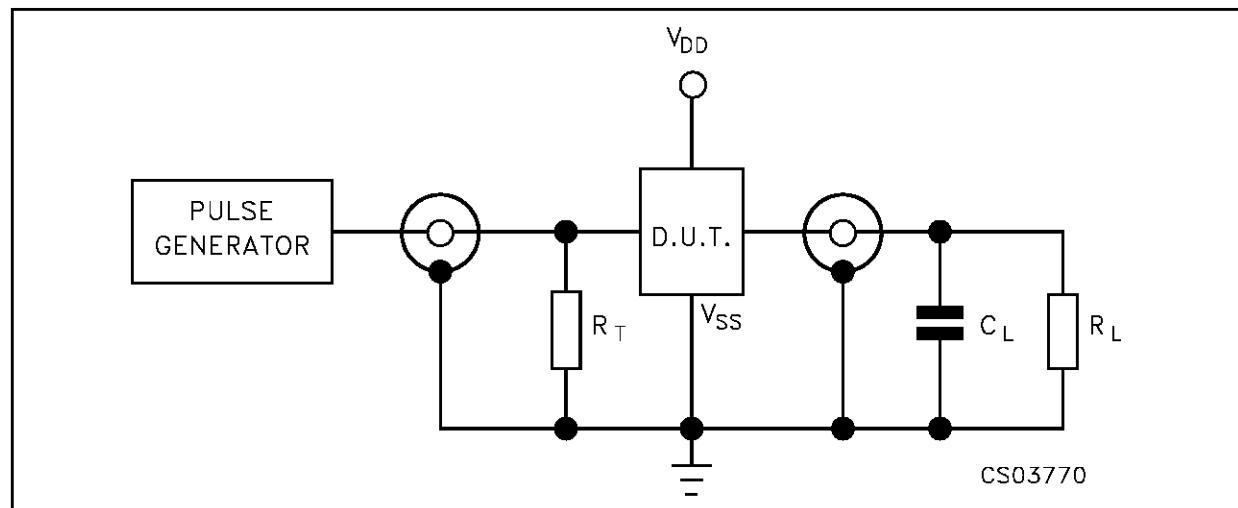
Symbol	Parameter	Test Condition				Value						Unit	
		$V_I$ (V)	$V_O$ (V)	$ I_{OL} $ ( $\mu$ A)	$V_{DD}$ (V)	$T_A = 25^\circ C$			$-40 \text{ to } 85^\circ C$		$-55 \text{ to } 125^\circ C$		
						Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
$I_L$	Quiescent Current	0/5			5		0.02	1		30		30	$\mu A$
		0/10			10		0.02	2		60		60	
		0/15			15		0.02	4		120		120	
		0/18			18		0.04	20		600		600	
$V_{OH}$	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
$V_{OL}$	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
$V_{IH}$	High Level Input Voltage	0.5/4.5	<1	5	3.5				3.5		3.5		V
		1/9	<1	10	7				7		7		
		1.5/13.5	<1	15	11				11		11		
$V_{IL}$	Low Level Input Voltage	4.5/0.5	<1	5				1.5		1.5		1.5	V
		9/1	<1	10				3		3		3	
		13.5/1.5	<1	15				4		4		4	
$I_{OH}$	Output Drive Current	0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		mA
		0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
$I_{OL}$	Output Sink Current	0/5	0.4	<1	5	0.44	1		0.36		0.36		mA
		0/10	0.5	<1	10	1.1	2.6		0.9		0.9		
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
$I_I$	Input Leakage Current	0/18	Any Input		18		$\pm 10^{-5}$	$\pm 0.1$		$\pm 1$		$\pm 1$	$\mu A$
$I_{OZ}$	3-State Output	0/18	0/18		18		$\pm 10^{-4}$	$\pm 0.4$		$\pm 12$		$\pm 12$	$\mu A$
$C_I$	Input Capacitance		Any Input				5	7.5					pF

The Noise Margin for both "1" and "0" level is: 1V min. with  $V_{DD}=5V$ , 2V min. with  $V_{DD}=10V$ , 2.5V min. with  $V_{DD}=15V$

**DYNAMIC ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25^{\circ}\text{C}$ ,  $C_L = 50\text{pF}$ ,  $R_L = 200\text{K}\Omega$ ,  $t_r = t_f = 20\text{ ns}$ )

Symbol	Parameter	Test Condition		Value (*)			Unit
		$V_{DD}$ (V)		Min.	Typ.	Max.	
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time (SET or RESET to Q)	5			150	300	ns
		10			70	140	
		15			50	100	
$t_{PZH}$ $t_{PZL}$	3-State Propagation Delay Time (Enable to Q)	5			115	230	ns
		10			55	110	
		15			40	80	
$t_{PLZ}$ $t_{PHZ}$	3-State Propagation Delay Time (Disable to Q)	5			90	180	ns
		10			50	100	
		15			35	70	
$t_{TLH}$ $t_{THL}$	Transition Time	5			100	200	ns
		10			50	100	
		15			40	80	
$t_W$	Pulse Width (Set or Reset)	5			160	80	ns
		10			80	40	
		15			40	20	

(\*) Typical temperature coefficient for all  $V_{DD}$  value is 0.3 %/ $^{\circ}\text{C}$ .

**TEST CIRCUIT**

$C_L = 50\text{pF}$  or equivalent (includes jig and probe capacitance)

$R_L = 200\text{K}\Omega$

$R_T = Z_{OUT}$  of pulse generator (typically 50 $\Omega$ )